ma-N 400 and ma-N 1400 — Negative Tone Photoresists

Unique features

- High wet and dry etch resistance
- Good thermal stability of the resist pattern
- Tunable pattern profile: vertical to undercut
- Aqueous alkaline development
- Easy to remove
- Based on safe solvents
- Resists available in a variety of viscosities

Applications

- Microelectronics and micro systems technology
- Mask for lift-off processes
- Etch mask for semiconductors and metals
- Well suitable for implantation

Technical data

<table>
<thead>
<tr>
<th>Resist</th>
<th>ma-N 400 µm</th>
<th>ma-N 1400 µm</th>
</tr>
</thead>
<tbody>
<tr>
<td>ma-N 405</td>
<td></td>
<td>ma-N 1405</td>
</tr>
<tr>
<td>ma-N 415</td>
<td>0.5</td>
<td>0.5</td>
</tr>
<tr>
<td>ma-N 420</td>
<td>1.5</td>
<td>0.7</td>
</tr>
<tr>
<td>ma-N 440</td>
<td>4.1</td>
<td>1.0</td>
</tr>
<tr>
<td>ma-N 490</td>
<td>7.5</td>
<td></td>
</tr>
</tbody>
</table>

Film thickness

- ma-N 400, 2 µm thick
- ma-N 1400, 2 µm thick

Spin coating / time

- 3000 rpm, 30 s

Spectral sensitivity

- 300 - 380 nm
- 300 - 410 nm

Thermal stability

- up to 110 °C, for metal evaporation
- up to 160 °C, for metal evaporation and sputtering